

Serial No.

Docket No.: RD-25,993-7

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re application of: Barry Lee-Mean Yang et al.  
Serial No.:  
Filed:  
Group Art Unit:

For: MULTILAYER ARTICLE AND METHOD OF MAKING BY ARC PLASMA DEPOSITION

INFORMATION DISCLOSURE STATEMENT

Honorable Assistant Commissioner of Patents  
Washington, DC 20231

SIR:

This Information Disclosure Statement is being filed under 37 C.F.R. §1.56 for a Continuation Application, which relies on the filing date of its parent application, such parent application being identified as:

U.S. Patent Application Serial No: 09/271,654

Examiner: M. Padgett

Filed: March 17, 1999

Allowed Date: 11/7/01

Inventor(s): Barry Lee-Mean Yang et al.

Issue Batch No. O58

Title: MULTILAYER ARTICLE AND METHOD OF MAKING BY ARC PLASMA DEPOSITION

Enclosed are copies of forms PTO-1449 and PTO-892 listing all "prior art" cited and submitted in the parent application. Pursuant to 37 C.F.R. §1.98(d), no actual copies of the documents listed are being furnished to the PTO with this Information Disclosure Statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Robert P. Santandrea".

Robert P. Santandrea  
Attorney

DATE: December 4, 2001

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RD-25,993

SERIAL NO.

09/271,654

INFORMATION DISCLOSURE STATEMENT BY APPLICANT--

LIST OF ITEMS

(Use several sheets if necessary)

Applicant

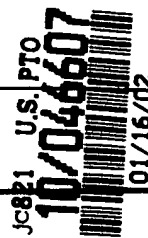
Barry Lee-Mean Yang et al.

Filing Date

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	AB 3 2 2 0 9 7 3	11/30/65	Goldberg			
	AC 3 3 1 2 6 5 9	04/04/67	Kurkky et al.			
	AD 3 3 1 2 6 6 0	04/04/67	Kurkky et al.			
	AE 3 3 1 3 7 7 7	04/11/67	Elam et al.			
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	AG 3 6 6 6 6 1 4	06/24/69	Snedeker et al.			
	AH 3 9 8 9 6 7 2	11/02/76	Vestergaard			
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						YES	No
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	AM 8 9 0 1 9 5 7	08/22/88	PCT				
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	BL						
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BR	
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	CC 5 4 6 3 0 1 3	10/31/95	Tokuda et al.			
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	CH 5 6 3 5 0 8 7	06/03/97	Schiller et al.			
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	CJ					
	CK					

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	CL						
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